HFZT

FMMT449

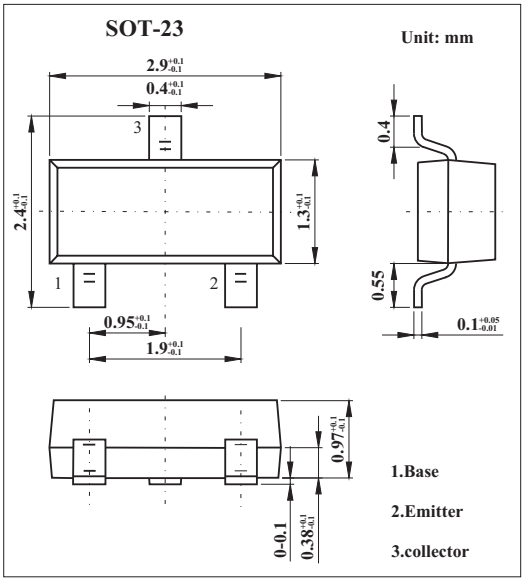
SOT-23 Plastic-Encapsulate Transistors

Features

- Low equivalent on-resistance.
- Medium Power Transistor

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	5	V
Peak collector current	I_{CM}	2	A
Collector current	I_C	1	A
Base current	I_B	200	mA
Power dissipation	P_{tot}	500	mW
Operating and storage temperature range	T_j,T_{stg}	-55 to +125	℃

PACKAGE INFORMATION

Device	Package	Shipping
FMMT4124	SOT-23	3000/Tape&Reel

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=1mA,I_E=0	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=10mA,I_B=0	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA,I_C=0	5			V
Collector cutoff current	I_{CBO}	V_{CB}=40V,I_E=0			0.1	μA
		V_{CB}=40V,Tam$_B$=100℃			10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=4V,I_C=0			0.1	μA
Collector-emitter saturation voltage *	$V_{CE(sat)}$	I_C=1A,I_B=100mA I_C=2A,I_B=200mA			0.5 1.0	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	I_C=1A,I_B=100mA			1.25	V
Base-emitter voltage *	$V_{BE(ON)}$	I_C=1A,V_{CE}=2V			1.0	V
Static Forward Current Transfer Ratio	h_{FE}	I_C=50mA, V_{CE}=2V*	70			
		I_C=500mA, V_{CE}=2V*	100		300	
		I_C=1A, V_{CE}=2V*	80			
		I_C=2A, V_{CE}=2V*	40			
Current-gain-bandwidth product	f_T	I_C=50mA,V_{CE}=10V,f=100MHz	150			MHz
Output capacitance	C_{obo}	V_{CB}=10V,f=1MHz			15	pF

* Pulse width=300μs. Duty cycle ≤2%

■ Marking

Marking	449